

L Number	Hits	Search Text	DB	Time stamp
1	88844	sram or dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:21
2	77367	(capacitor or dielectric) near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:23
3	8651	((sram or dram) and ((capacitor or dielectric) near5 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:26
4	4	l1d and bitline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:34
5	200	l1d and bitline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:36
6	463	bitline same implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:38
7	129	((sram or dram) and ((capacitor or dielectric) near5 substrate)) and (bitline same implant\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/14 15:39